



SOT-89 Plastic-Encapsulate Transistors

2SA1797 TRANSISTOR (PNP)

FEATURES

- Low saturation voltage
- Excellent DC current gain characteristics
- Complements to 2SC4672

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

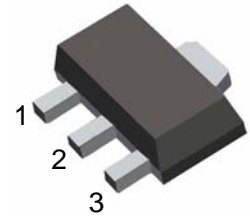
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-2	A
P_C	Collector Power dissipation	500	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}$, $I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$, $I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}$, $I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}$, $I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}$, $I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2\text{V}$, $I_C=-500\text{mA}$	82		270	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1\text{A}$, $I_B=-50\text{mA}$			-0.35	V
Transition frequency	f_T	$V_{CE}=-2\text{V}$, $I_C=-0.5\text{A}$, $f=100\text{MHz}$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}$, $I_E=0$, $f=1\text{MHz}$		36		pF

CLASSIFICATION OF h_{FE}

Rank	P	Q
Range	82-180	120-270
Marking	AGP	AGQ

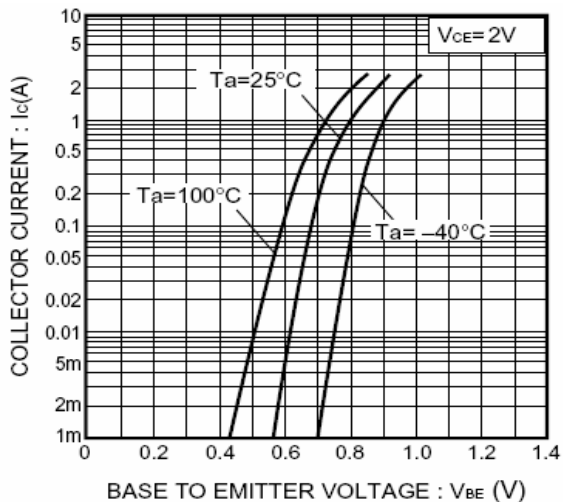


Fig.1 Grounded emitter propagation characteristics

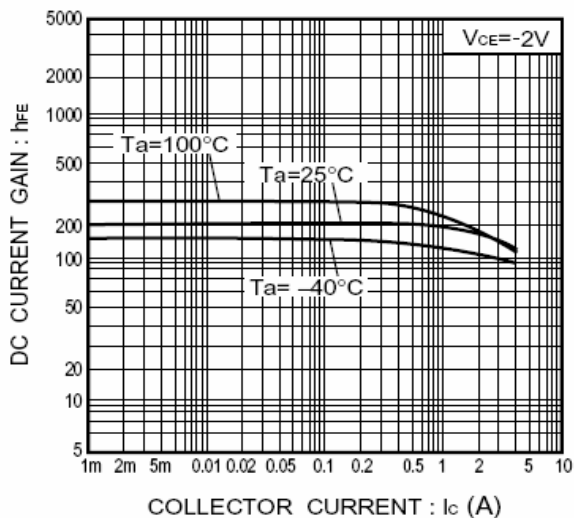


Fig.2 DC current gain vs. collector current

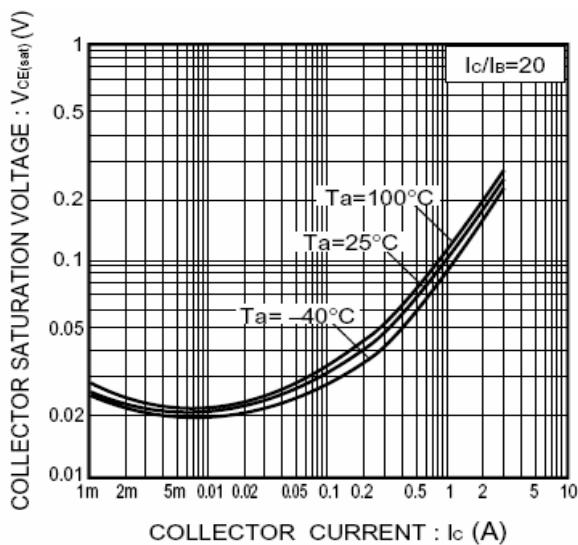


Fig.3 Collector-emitter saturation voltage vs. collector current

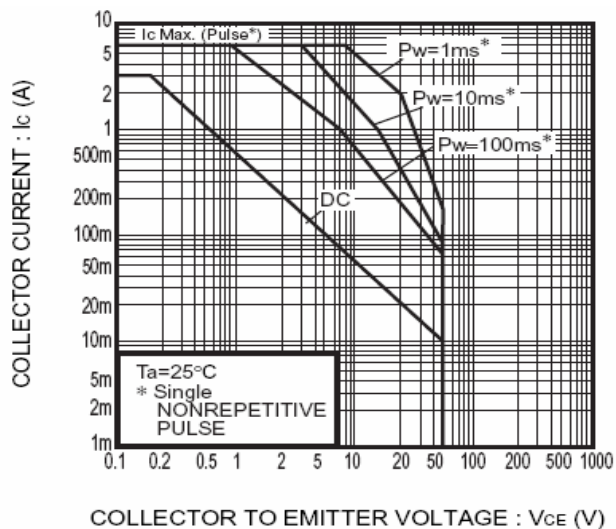


Fig.4 Safe Operating area